

TOSHIBA BIPOLAR DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TD62501P, TD62501F, TD62502P, TD62502F, TD62503P, TD62503F, TD62504P
TD62504F, TD62505P, TD62505F, TD62506P, TD62506F, TD62507P, TD62507F

7 SINGLE DRIVER

TD62501, 502, 503, 504P/F : COMMON EMITTER
TD62505, 506P/F : COMMON COLLECTOR
TD62507P/F : ISOLATED

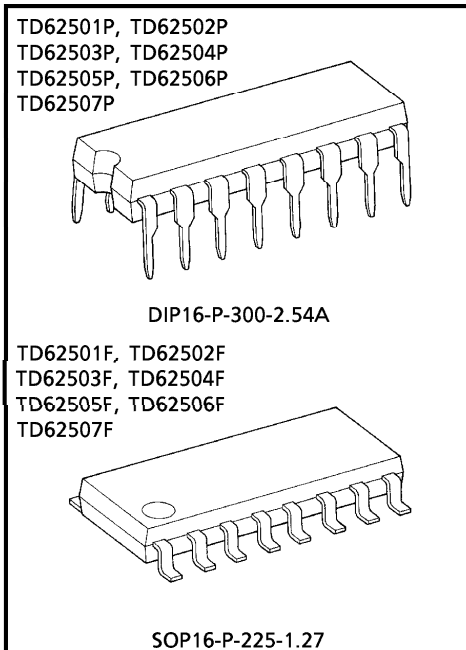
The TD62501P/F Series are comprised of seven or five NPN Transistor Arrays.

For proper operation, the substrate (SUB) must be connected to the most negative voltage.

Applications include relay, hammer, Lamp and display (LED) drivers.

FEATURES

- Output Current (Single Output) 200mA MAX.
- High Sustaining Voltage Output 35V MIN.
- Inputs Compatible with Various Types of Logic.
- TD62501P/F, TD62505P/F and TD62507P/F : Using external resistor...General Purpose
- TD62502P/F
: $R_{IN} = 10.5k\Omega + 7V$ Zener Diode... 14~25V P-MOS
- TD62503P/F, TD62506P/F : $R_{IN} = 2.7k\Omega$...TTL, 5V C-MOS
- TD62504P/F, : $R_{IN} = 10.5k\Omega$...6~15V P-MOS, C-MOS
- Package Type-p : DIP-16 pin
- Package Type-F : SOP-16 pin

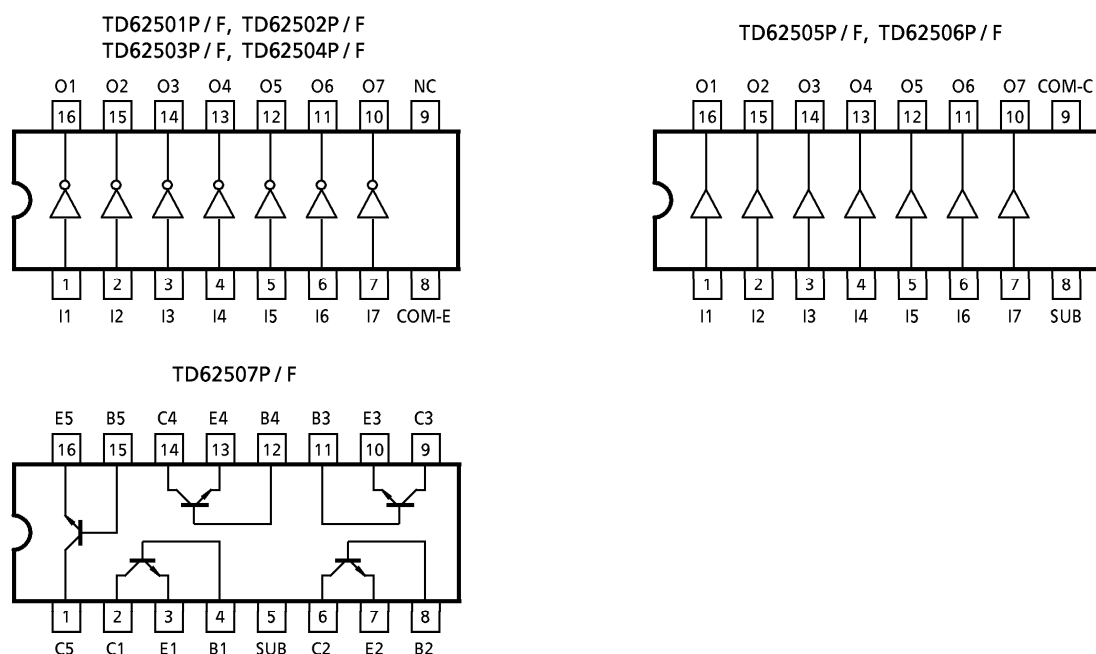


Weight
DIP16-P-300-2.54A : 1.11g (Typ.)
SOP16-P-225-1.27 : 0.16g (Typ.)

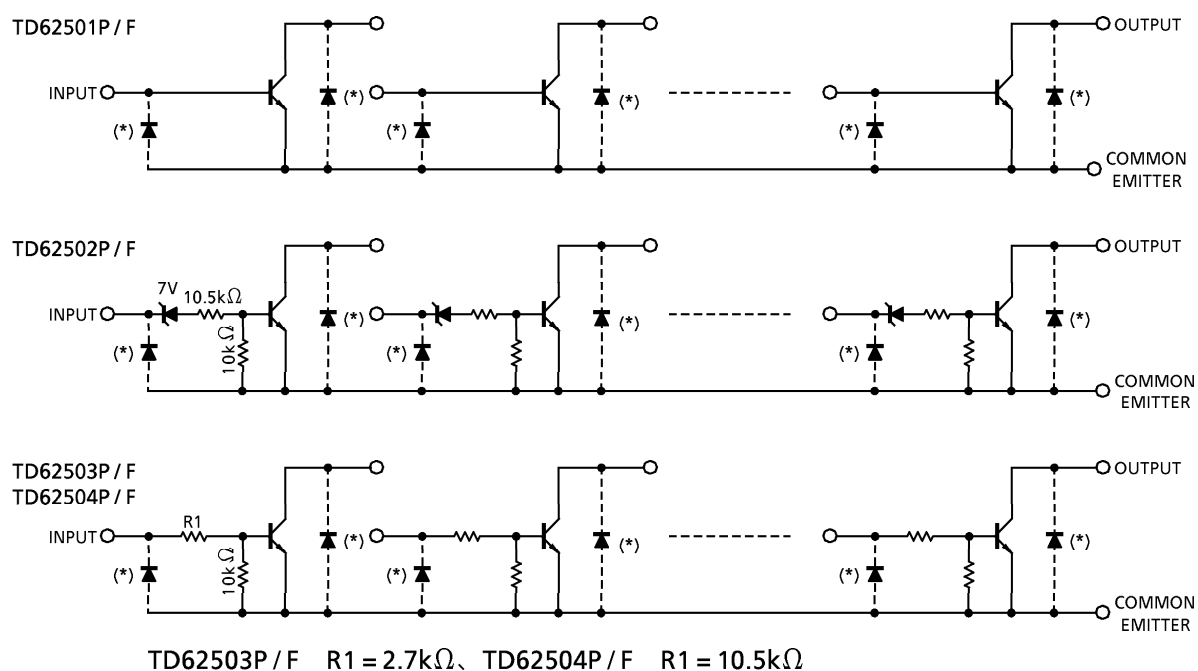
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PIN CONNECTION (Top view)

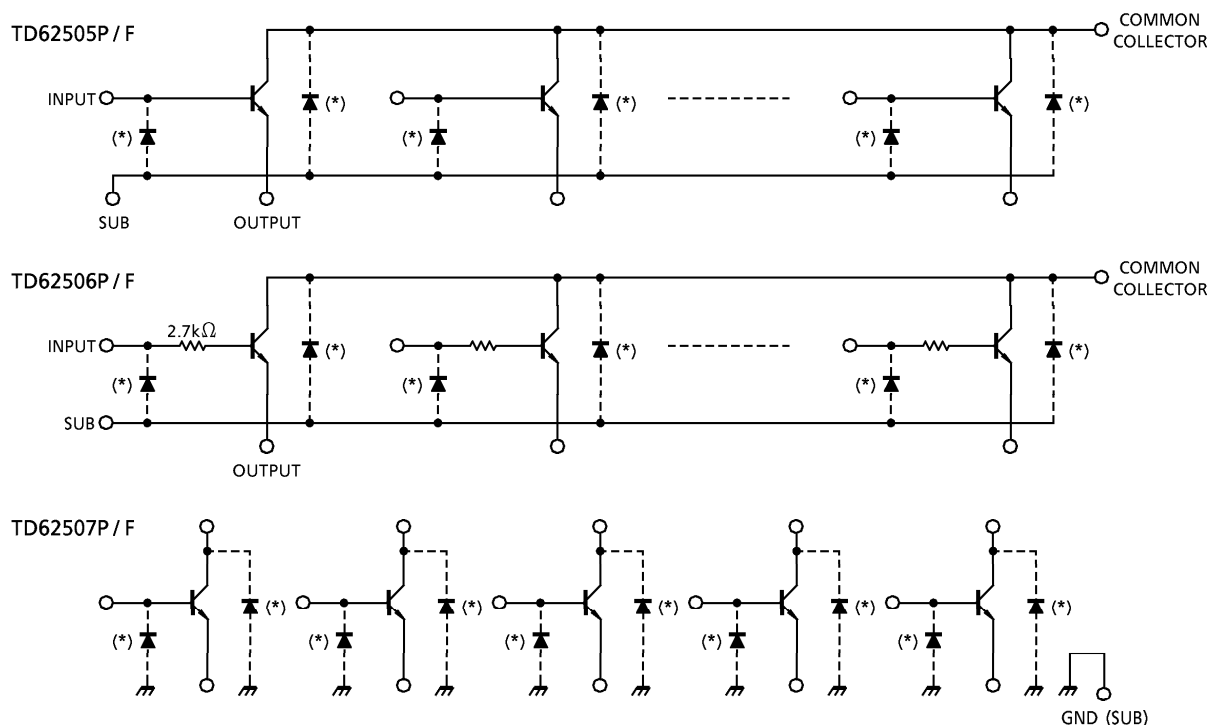


SCHEMATICS (Each driver)



(*) Parasitic Diodes

SCHEMATICS (Each driver)



(*) Parasitic Diodes

(Note) The input and output parasitic diodes cannot be used as clamp diodes.

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$ Unless otherwise noted)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		V_{CEO}	35	V
Collector-Base Voltage		V_{CBO}	50	V
Collector Current		I_C	200	mA / ch
Input Voltage		V_{IN} (Note 1)	- 0.5~45	V
		V_{IN} (Note 2)	- 0.5~30	
Input Current		I_{IN} (Note 3)	25	mA
Isolation Voltage		V_{SUB}	35	V
Power Dissipation	P	P_D	1.0	W
	F		0.625 (Note 4)	
Operating Temperature		T_{opr}	- 40~85	$^\circ\text{C}$
Storage Temperature		T_{stg}	- 55~150	$^\circ\text{C}$

(Note 1) TD62506P / F

(Note 2) TD62502P / F, TD62503P / F, TD62504P / F

(Note 3) TD62501P / F, TD62505P / F, TD62507P / F

(Note 4) On Glass Epoxy PCB (30 × 30 × 1.6mm, Cu 50%)

RECOMMENDED OPERATING CONDITIONS (Ta = -40~85°C)

CHARACTERISTIC		SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Voltage		V _{CEO}		0	—	35	V
Collector-Base Voltage		V _{CBO}		0	—	50	V
Collector Current		I _C		0	—	150	mA / ch
Input Voltage	TD62506P / F	V _{IN}		0	—	35	V
	TD62502P / F						
	TD62503P / F		0	—	25		
	TD62504P / F						
Input Current	TD62501P / F	I _{IN}		0	—	10	mA
	TD62505P / F						
	TD62507P / F						
Power Dissipation	P	P _D		—	—	0.360	W
	F		On PCB (*)	—	—	0.325	

(*) 30 × 30 × 1.6mm, Cu 50%

ELECTRICAL CHARACTERISTICS (Ta = 25°C Unless otherwise noted)

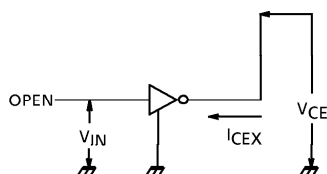
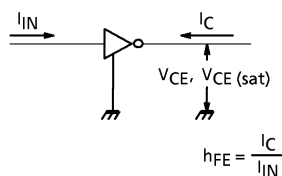
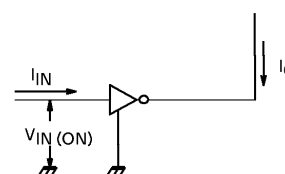
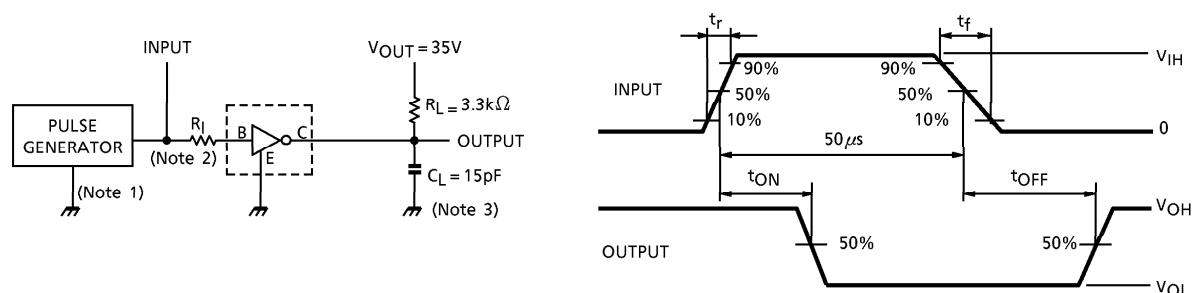
CHARACTERISTIC		SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Leakage Current		I_{CEX}	1	$V_{CE} = 25V, V_{IN} = 0$	—	—	10	μA
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	2	$I_{IN} = 1mA, I_C = 10mA$	—	—	0.2	V
				$I_{IN} = 3mA, I_C = 150mA$ (Note 1)	—	—	0.8	
DC Current Transfer Ratio	(Note 2)	h_{FE}	2	$V_{CE} = 10V, I_C = 10mA$	70	—	—	
	(Note 3)				50	—	—	
Input Voltage	TD62502P / F	$V_{IN(ON)}$	3	$I_{IN} = 1mA$ $I_C = 10mA$	13	17	23	V
	TD62503P / F				2.4	3.4	4.2	
	TD62504P / F				7.5	11.5	15	
Turn-On Delay		t_{ON}	4	$V_{OUT} = 35V, R_L = 3.3k\Omega$ $C_L = 15pF$	—	50	—	ns
Turn-Off Delay		t_{OFF}			—	200	—	

(Note 1) Except TD62502P / F Only

(Note 2) Only TD62501P / F, TD62505P / F, TD62506P / F, TD62507P / F

(Note 3) Only TD62502P / F, TD62503P / F, TD62504P / F

TEST CIRCUIT

1. I_{CEX} 2. h_{FE} , $V_{CE(sat)}$ 3. $V_{IN(ON)}$ 4. t_{ON} , t_{OFF} 

(Note 1) Pulse Width $50\mu s$, Duty Cycle 10%
Output Impedance 50Ω , $t_r \leq 5ns$, $t_f \leq 10ns$

(Note 2) See below

INPUT CONDITION

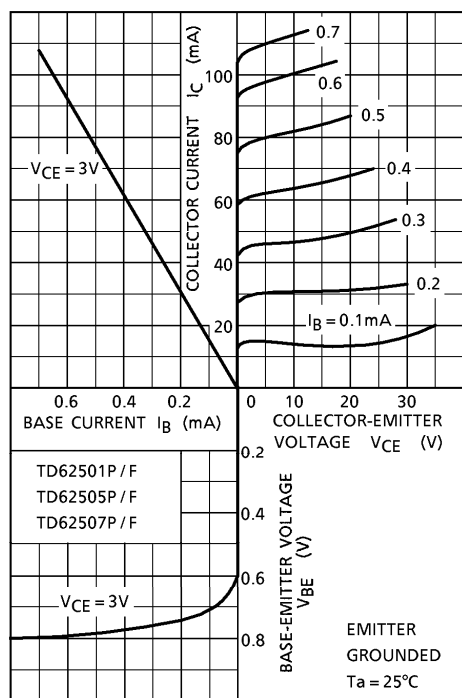
TYPE NUMBER	R_I	V_{IH}
TD62501P / F	$2.7k\Omega$	3V
TD62502P / F	0Ω	15V
TD62503P / F	0Ω	3V
TD62504P / F	0Ω	10V
TD62505P / F	$2.7k\Omega$	3V
TD62506P / F	0Ω	3V
TD62507P / F	$2.7k\Omega$	3V

(Note 3) C_L includes probe and jig capacitance

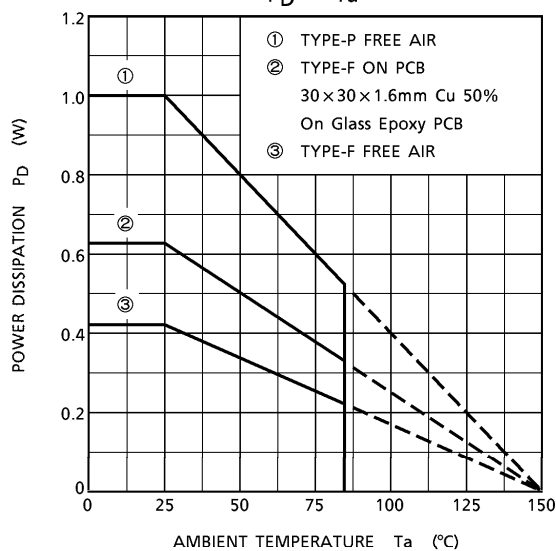
PRECAUTIONS for USING

Utmost care is necessary in the design of the output line, V_{CC} and GND line since IC may be destroyed due to short-circuit between outputs, air contamination fault, or fault by improper grounding.

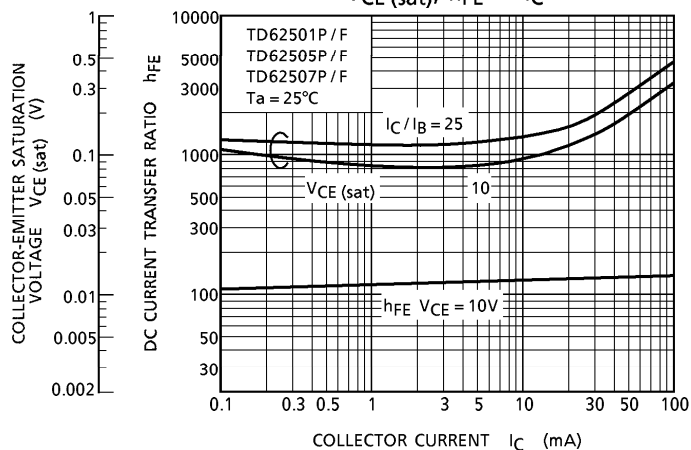
STATIC CHARACTERISTICS

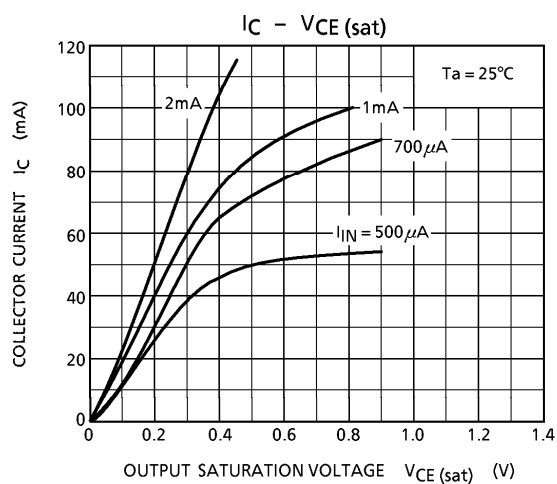
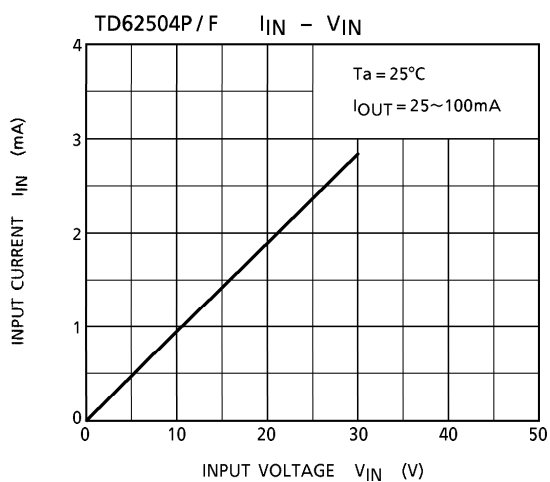
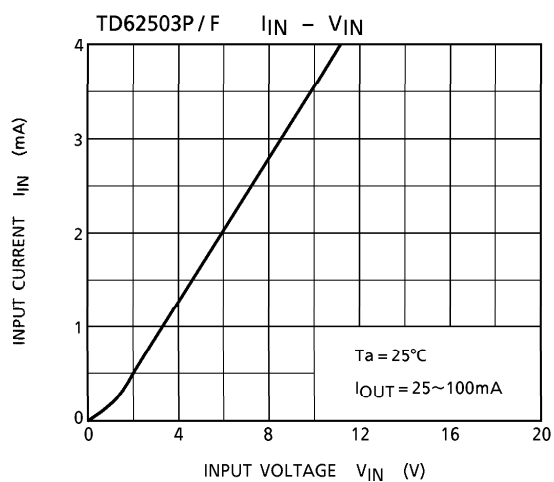
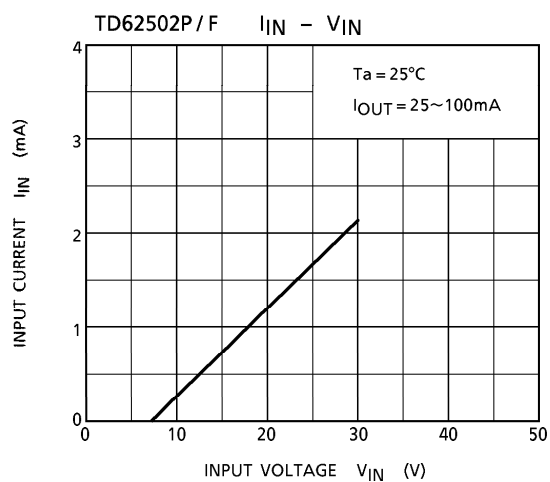
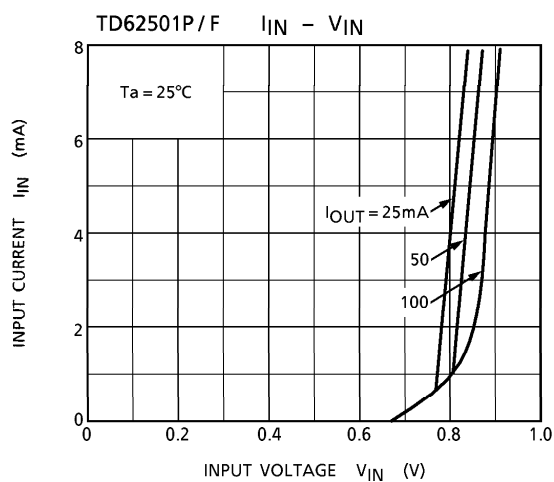


$P_D - T_a$



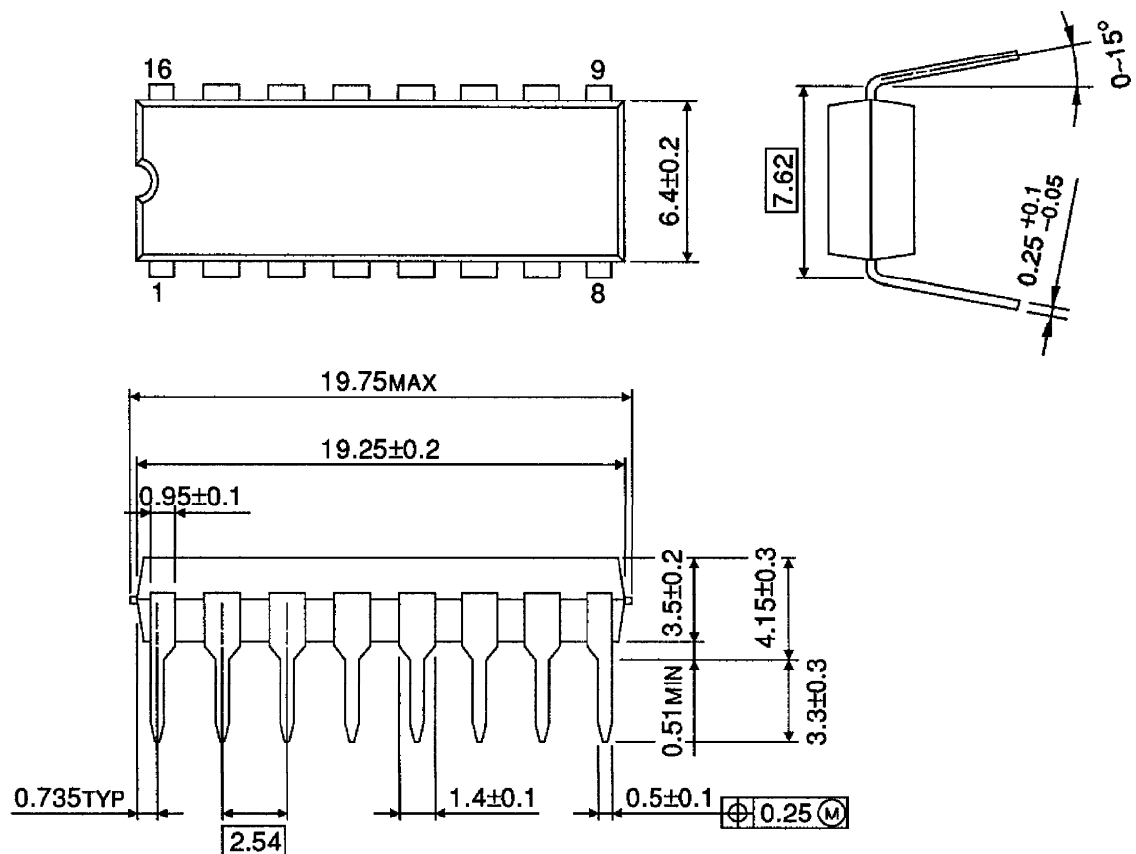
$V_{CE(sat)}, h_{FE} - I_C$





OUTLINE DRAWING
DIP16-P-300-2.54A

Unit : mm



Weight : 1.11g (Typ.)

